

# NJ5N65 POWER MOSFET

## 5.0A 650V N-CANNEL POWER MOSFET



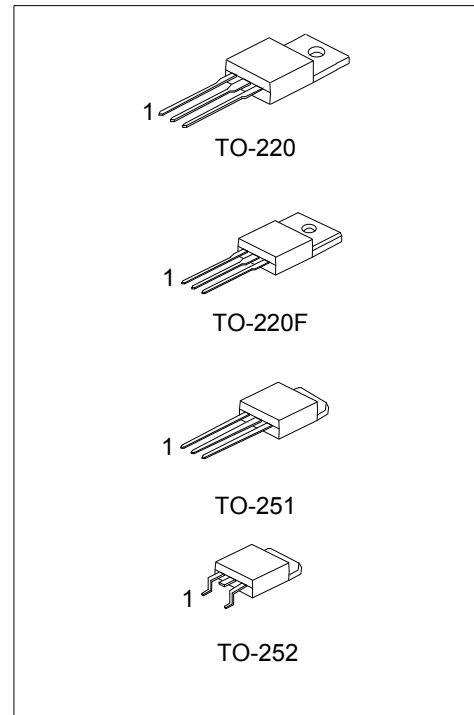
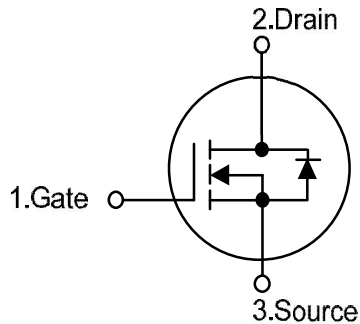
### DESCRIPTION

The NJ5N65 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

### FEATURES

- \*  $V_{DS} = 650V$
- \*  $I_D = 5.0A$
- \*  $R_{DS(ON)} = 2.5\Omega @ V_{GS} = 10V$ .
- \* Ultra Low gate charge (typical 15nC)
- \* Low reverse transfer capacitance ( $C_{RSS} =$  typical 6.5 pF)
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness

### SYMBOL



### ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
NJ5N65-LI	TO-220	G	D	S	Tape Box
NJ5N65-BL	TO-220	G	D	S	Bulk
NJ5N65F-LI	TO-220F	G	D	S	Tube
NJ5N65A-LI	TO-251	G	D	S	Tube
NJ5N65D-TR	TO-252	G	D	S	Tape Ree
NJ5N65D-LI	TO-252	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

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## ■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	650	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Avalanche Current (Note 2)		$I_{AR}$	4.5	A
Continuous Drain Current		$I_D$	4.5	A
Pulsed Drain Current (Note 2)		$I_{DM}$	18	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	210	mJ
	Repetitive (Note 2)	$E_{AR}$	10	
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220	$P_D$	100	W
	TO-220F		36	
	TO-251 / TO-252		54	
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Operation Temperature		$T_{OPR}$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by  $T_{J(MAX)}$

3.  $L = 18.9\text{mH}$ ,  $I_{AS} = 4.5\text{ A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 4.5\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

## ■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
	TO-220F		62.5	
	TO-251 / TO-252		160	
Junction to Case	TO-220	$\theta_{JC}$	1.25	$^\circ\text{C}/\text{W}$
	TO-220F		3.47	
	TO-251 / TO-252		2.3	

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## ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise specified)

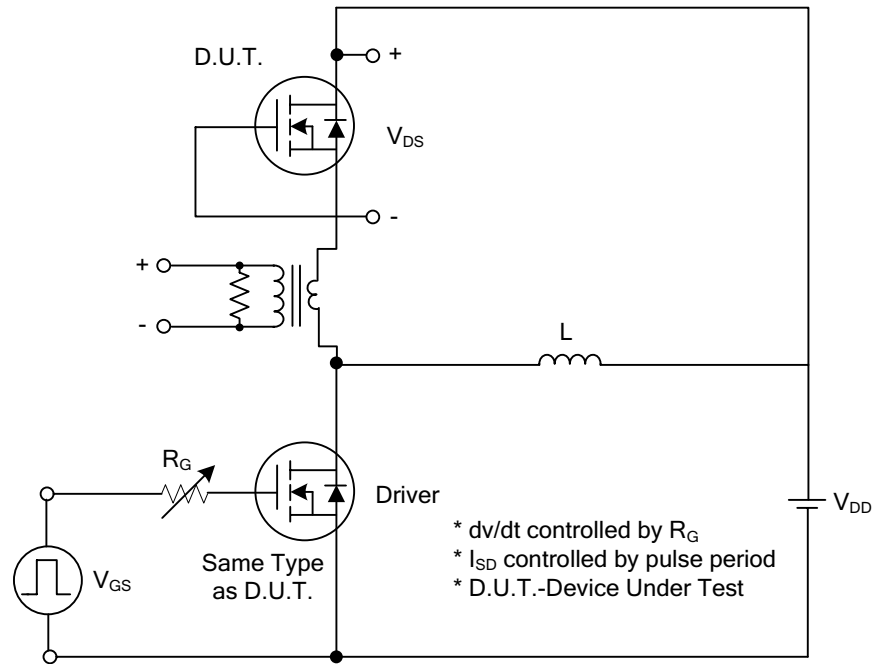
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	650			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = 650V, V <sub>GS</sub> = 0V			1	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>			100	nA
	Reverse				-100	
Breakdown Voltage Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> = 250μA, Referenced to 25°C		0.6		V/°C
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.25A		2.0	2.5	Ω
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz		515	670	pF
Output Capacitance	C <sub>OSS</sub>			55	72	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			6.5	8.5	pF
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 325V, I <sub>D</sub> = 4.5 A, R <sub>G</sub> = 25Ω (Note 1, 2)		10	30	ns
Turn-On Rise Time	t <sub>R</sub>			42	90	ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			38	85	ns
Turn-Off Fall Time	t <sub>F</sub>			46	100	ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DS</sub> = 520 V, I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 10 V (Note 1, 2)		15	19	nC
Gate-Source Charge	Q <sub>GS</sub>			2.5		nC
Gate-Drain Charge	Q <sub>GD</sub>			6.6		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 4.5 A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>				4.5	A
Maximum Pulsed Drain-Source Diode Forward Current	I <sub>SM</sub>				18	A
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 4.5 A, dI <sub>F</sub> / dt = 100 A/μs (Note 1)		300		ns
Reverse Recovery Charge	Q <sub>RR</sub>			2.2		μC

Note 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%

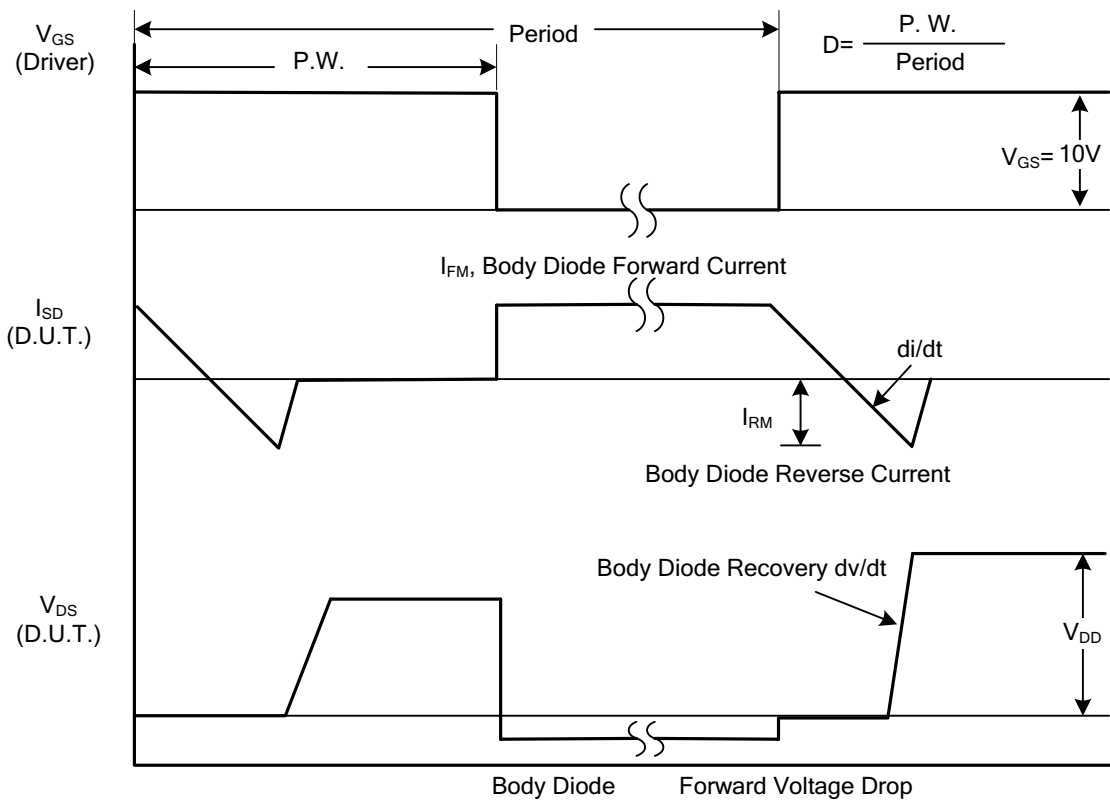
2. Essentially independent of operating temperature

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## ■ TEST CIRCUITS AND WAVEFORMS



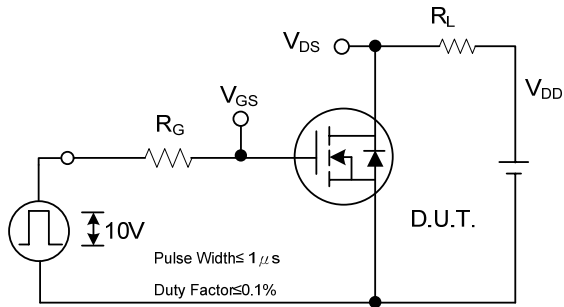
Peak Diode Recovery  $dv/dt$  Test Circuit



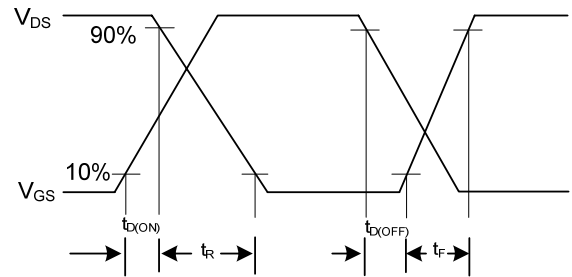
Peak Diode Recovery  $dv/dt$  Waveforms

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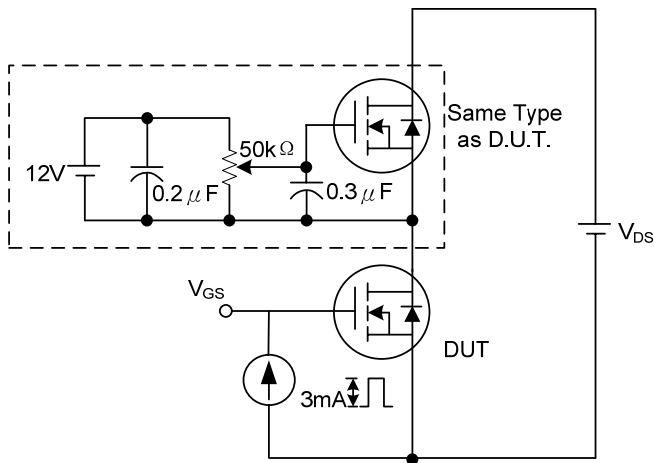
## ■ TEST CIRCUITS AND WAVEFORMS (Cont.)



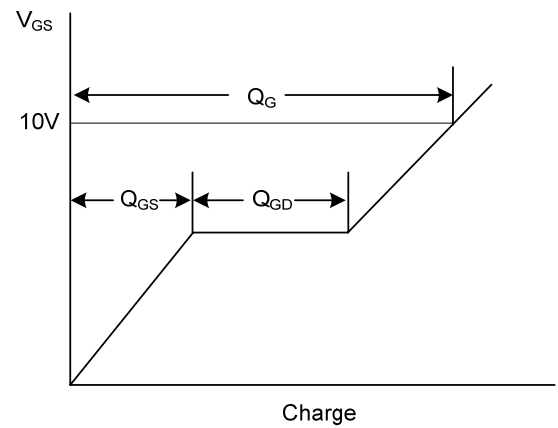
**Switching Test Circuit**



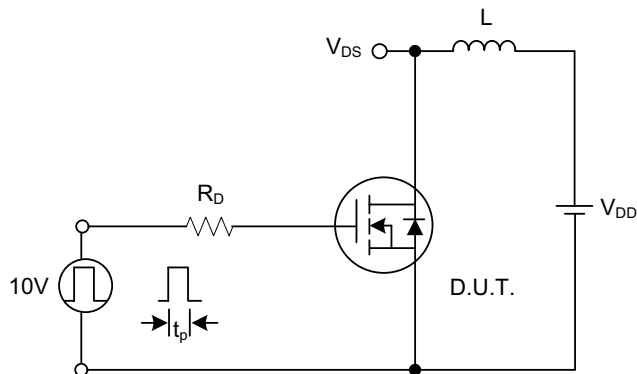
**Switching Waveforms**



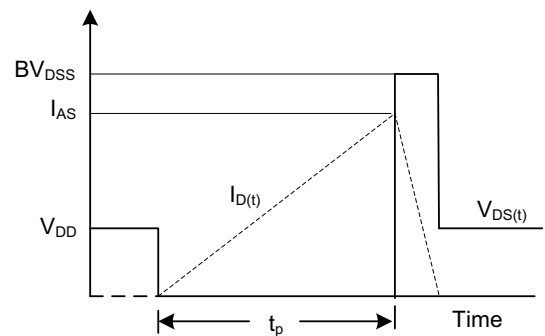
**Gate Charge Test Circuit**



**Gate Charge Waveform**



**Unclamped Inductive Switching Test Circuit**



**Unclamped Inductive Switching Waveforms**

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## TYPICAL CHARACTERISTICS

